

Sub C-1 flattening said substrate by vacuum-sucking said substrate onto a stage having a flat surface in such a manner that said lower surface of said substrate is in contact with said flat surface of the stage; and

Amended irradiating said semiconductor film with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam[,]\_

[wherein roughness and waviness of the surface of the flattened substrate are 5  $\mu$  m or less, respectively.]

Sub C-2 10. (Amended) A method of manufacturing a liquid crystal display device comprising the steps of:

C-2 forming a semiconductor film over a substrate having an upper surface and a lower surface, wherein said upper surface is an insulating surface;

flattening said substrate by vacuum-sucking said substrate onto a stage having a flat surface and at least one suction inlet in such a manner that said lower surface of said substrate is in contact with said flat surface of the stage; and

*3*  
*12*  
*C2 end*  
irradiating said semiconductor film with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam[,].

[wherein a difference in level of the surface of the flattened substrate is at least a focal depth of the laser beam or less.]

*3*  
*Sub D3*  
13. (Amended) A method of manufacturing a liquid crystal display device comprising the steps of:

forming a semiconductor film over a substrate having an upper surface and a lower surface, wherein said upper surface is an insulating surface;

*C3*  
heating said substrate;

flattening said substrate by vacuum-sucking said substrate onto a stage having a flat surface in such a manner that said lower surface of said substrate is in contact with said flat surface of the stage; and

irradiating said semiconductor film with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam[,].

*C3 amend*  
[wherein roughness and waviness of the surface of the flattened substrate are 5  $\mu$ m or less, respectively.]

*Sub C4 D4*  
16. (Amended) A method of manufacturing a liquid crystal display device comprising the steps of:

forming a semiconductor film over a substrate having an upper surface and a lower surface, wherein said upper surface is an insulating surface;

heating said substrate;

*C4*  
flattening said substrate by vacuum-sucking said substrate onto a stage having a flat surface and at least one suction inlet in such a manner that said lower surface of said substrate is in contact with said flat surface of the stage; and

irradiating said semiconductor film with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam[,].

[wherein a difference in level of the surface of the flattened substrate is at least a focal depth of the laser beam or less.]

*Sub C5 D5*  
*C5*  
19. (Amended) A method of manufacturing a liquid crystal display device comprising the steps of:

forming a semiconductor film over a substrate having an upper surface and a lower surface, wherein said upper surface is an insulating surface;

Sub  
C6  
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heating substrate to crystallize said semiconductor film;  
flattening said substrate by vacuum-sucking said substrate onto a stage having a flat surface in such a manner that said lower surface of said substrate is in contact with said flat surface of the stage; and

irradiating the crystallized semiconductor film with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam[.].

[wherein roughness and waviness of the surface of the flattened substrate are 5  $\mu$ m or less, respectively.]

Sub  
C6  
22. (Amended) A method of manufacturing a liquid crystal display device comprising the steps of:

forming a semiconductor film over a substrate having an upper surface and a lower surface, wherein said upper surface is an insulating surface;

heating substrate to crystallize said semiconductor film;  
flattening said substrate by vacuum-sucking said substrate onto a stage having a flat surface and at least one suction

*Sub  
file*  
*C6 end*  
inlet in such a manner that said lower surface of said substrate is in contact with said flat surface of the stage; and

irradiating the crystallized semiconductor film with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam[,].

[wherein a difference in level of the surface of the flattened substrate is at least a focal depth of the laser beam or less.]

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25. (Amended) A method of manufacturing a liquid crystal display device comprising the steps of:

forming a semiconductor film over a substrate having an insulating surface;

*C7*  
heating said substrate and said semiconductor film, wherein said heating deforms said substrate and said semiconductor film from flat to curved;

flattening said substrate by cooling; and

irradiating said semiconductor film with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam[,].

Cyberel [wherein roughness and waviness of the surface of the flattened substrate are 5  $\mu$  m or less, respectively.]

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28. (Amended) A method of manufacturing a liquid crystal display device comprising the steps of:

forming a semiconductor film over a substrate having an insulating surface;

heating said substrate to crystallize said semiconductor film, wherein said heating deforms said substrate and said semiconductor film from flat to curved;

Cg flattening said substrate by cooling; and

irradiating the crystallized semiconductor film with a laser beam [having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam,

wherein roughness and waviness of the surface of the flattened substrate are 5  $\mu$  m or less, respectively.]

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[Please add the following new claims:]

Cg Sub D7 31. (New) A method of manufacturing a liquid crystal display device comprising:

forming a semiconductor film over a substrate having an upper surface and a lower surface, wherein said upper surface is an insulating surface;

flattening said substrate by vacuum-sucking said substrate onto a stage having a flat surface in such a manner that said lower surface of said substrate is in contact with said flat surface of the stage;

irradiating said semiconductor film with a laser beam.

32. (New) A method according to claim 31 wherein said laser beam is an excimer laser beam.

33. (New) A method according to claim 31 wherein at least a part of flattened substrate constitutes the liquid crystal display device.

34. (New) A method of manufacturing a liquid crystal display device comprising:

forming a semiconductor film over a substrate having an upper surface and a lower surface, wherein said upper surface is an insulating surface;

flattening said substrate by vacuum-sucking said substrate onto a stage having a flat surface and at least one suction

inlet in such a manner that said lower surface of said substrate is in contact with said flat surface of the stage; and irradiating said semiconductor film with a laser beam.

35. (New) A method according to claim 34 wherein said laser beam is an excimer laser beam.

36. (New) A method according to claim 34 wherein at least a part of flattened substrate constitutes the liquid crystal display device.

37. (New) A method according to claim 7 wherein said substrate is a glass substrate.

38. (New) A method according to claim 10 wherein said substrate is a glass substrate.

39. (New) A method according to claim 13 wherein said substrate is a glass substrate.

40. (New) A method according to claim 16 wherein said substrate is a glass substrate.